

ABSTRACT OF THE DISCLOSURE

The invention includes constructions having two dielectric layers over a conductively-doped semiconductive material. One of the dielectric layers contains aluminum oxide, and the other contains a metal oxide other than aluminum oxide (such metal oxide can be, for example, one or more of hafnium oxide, tantalum oxide, titanium oxide and zirconium oxide). The layer containing aluminum oxide is between the layer containing metal oxide and the conductively-doped semiconductive material. The invention includes capacitor devices having one electrode containing conductively-doped silicon and another electrode containing one or more metals and/or metal compounds. At least two dielectric layers are formed between the two capacitor electrodes, with one of the dielectric layers containing aluminum oxide and the other containing a metal oxide other than aluminum oxide. The invention also includes methods of forming capacitor constructions.